

SESDFBPxxV Series
Single Line ESD Protection Diode

Revision:B

General Description

The SESDFBPxxV ESD protection diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs.

Applications

- Cellular phones handsets and Accessories
- PDA's
- MP3 players
- Digital cameras
- Portable applications
- mobile telephone

Features

- 60W peak pulse power
- Small package for use in portable electronics
- Low leakage current
- These are Pb-Free Devices

Complies with the following standards

IEC61000-4-2

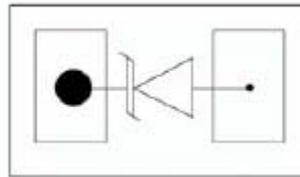
Level 4 15 kV (air discharge)

8 kV(contact discharge)

MIL STD 883E - Method 3015-7 Class 3

25 kV HBM (Human Body Model)

Functional diagram



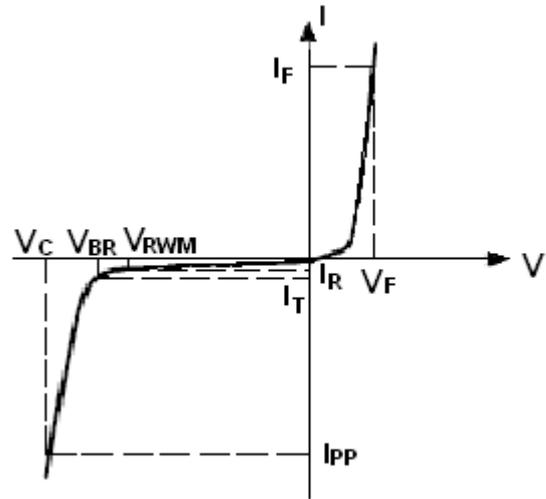
WBFBP-02C

Maximum Ratings

| Symbol | Parameter | Value | Unit |
|-----------------------------------|--|------------|------|
| V _{PP} | IEC 61000-4-2 (ESD) Contact | ±15 | kV |
| P _{PK} | Peak Pulse Power | 60 | W |
| I _{PP} | Peak Pulse Power | 12 | A |
| T _J , T _{STG} | Junction and Storage Temperature Range | -55 to 150 | °C |
| T _L | Lead Solder Temperature – Maximum (10 Second Duration) | 260 | °C |

Electrical Parameter

| Symbol | Parameter |
|-----------|---|
| I_{PP} | Maximum Reverse Peak Pulse Current |
| V_C | Clamping Voltage @ I_{PP} |
| V_{RWM} | Working Peak Reverse Voltage |
| I_R | Maximum Reverse Leakage Current @ V_{RWM} |
| I_T | Test Current |
| V_{BR} | Breakdown Voltage @ I_T |
| I_F | Forward Current |
| V_F | Forward Voltage @ I_F |



Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted, $V_F=1.25\text{V}$ Max. @ $I_F=10\text{mA}$ for all types)

| Part Numbers | V_{BR} | | | I_T | V_{RWM} | I_R | C |
|--------------|----------|------|------|-------|-----------|-------|-----------------------------|
| | Min. | Typ. | Max. | | | | Max. 1MHz, 0V Bias (note 1) |
| | V | V | V | | | | pF |
| SESDFBP3V3 | 5.0 | 5.7 | 6.4 | 1 | 3.3 | 1 | 35 |
| SESDFBP05V | 6.0 | 6.8 | 7.2 | 1 | 5.0 | 1 | 30 |
| SESDFBP07V | 7.5 | 8.1 | 8.6 | 1 | 7.0 | 1 | 25 |
| SESDFBP12V | 13.5 | 14.2 | 15.0 | 1 | 12.0 | 1 | 15 |

1. Capacitance of one diode at $f=1\text{MHz}$, $V_{RW}=0\text{V}$, $T_A=25^\circ\text{C}$

Typical Characteristics

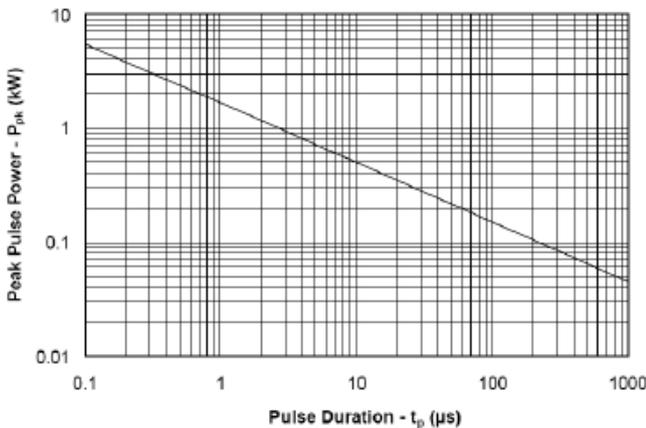


Figure 1. Non-Repetitive Peak Pulse Power versus Pulse Time

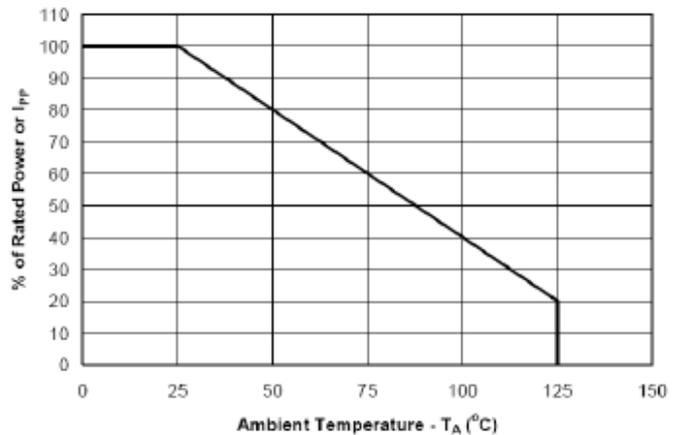


Fig 2. Power Derating Curve

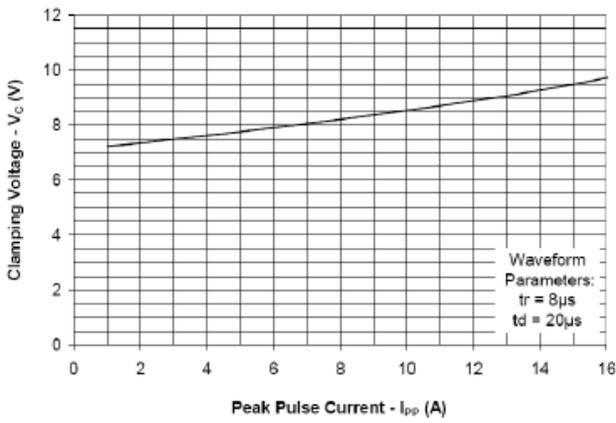


Figure 3. Clamping Voltage vs. Peak Pulse Current

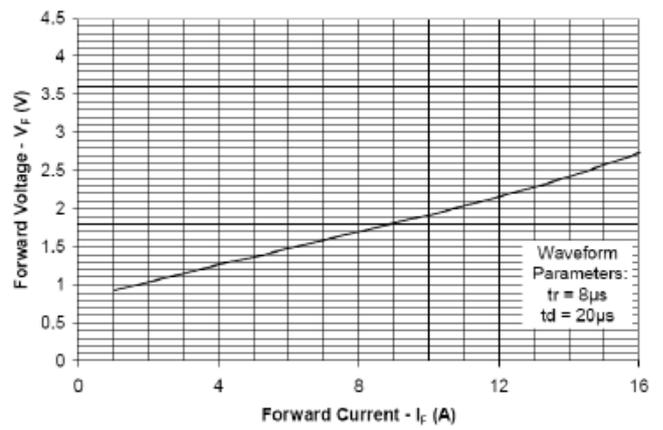


Figure 4. Forward Voltage vs. Forward Current

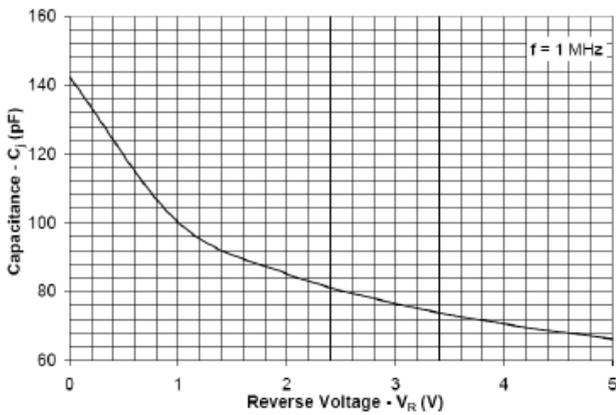


Figure 5. Junction Capacitance vs. Reverse Voltage

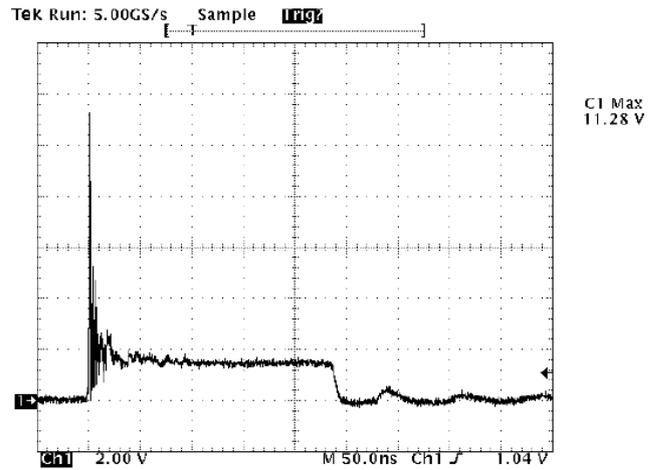
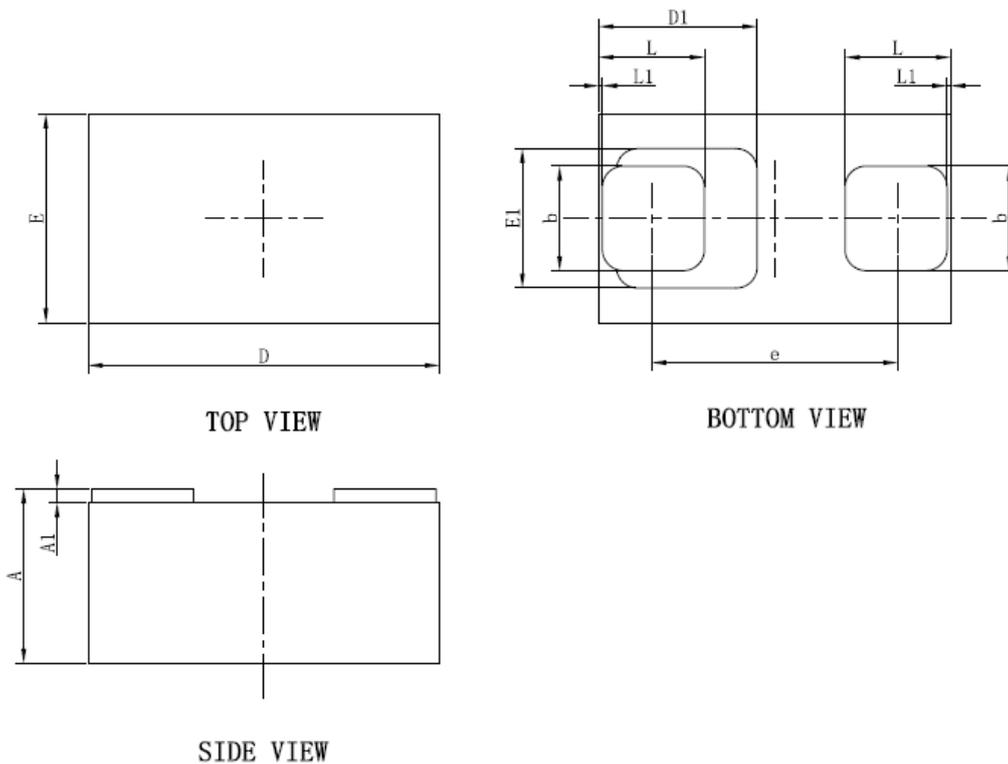


Fig 6. ESD Clamping (8kV Contact per IEC 61000-4-2)

WBFBP-02C Mechanical Data



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.450 | 0.550 | 0.018 | 0.022 |
| A1 | 0.010 | 0.070 | 0.000 | 0.003 |
| D | 0.950 | 1.050 | 0.037 | 0.041 |
| E | 0.550 | 0.650 | 0.022 | 0.026 |
| D1 | 0.450REF. | | 0.018REF. | |
| E1 | 0.400REF. | | 0.016REF. | |
| b | 0.275 | 0.325 | 0.011 | 0.013 |
| e | 0.675 | 0.725 | 0.027 | 0.029 |
| L | 0.275 | 0.325 | 0.011 | 0.013 |
| L1 | 0.010REF. | | 0.000REF. | |

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